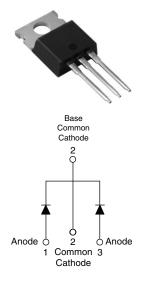
### Vishay High Power Products

## HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 2 x 4 A



#### TO-220AB

PRODUCT SUMMARY				
V <sub>R</sub>	600 V			
V <sub>F</sub> at 4 A at 25 °C	1.8 V			
I <sub>F(AV)</sub>	2 x 4 A			
t <sub>rr</sub> (typical)	17 ns			
T <sub>J</sub> (maximum)	150 °C			
Q <sub>rr</sub>	40 nC			
dI <sub>(rec)M</sub> /dt	280 A/µs			

### FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I<sub>RRM</sub>
- Very low Q<sub>rr</sub>
- Specified at operating conditions
- Designed and qualified for industrial level

#### BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

#### DESCRIPTION

HFA08TA60C is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A per leg continuous current, the HFA08TA60C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>BBM</sub>) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08TA60C is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V <sub>R</sub>		600	V	
Maximum continuous forward current	F	T <sub>C</sub> = 100 °C	4		
per device			8	А	
Single pulse forward current	I <sub>FSM</sub>		25	A	
Maximum repetitive forward current	I <sub>FRM</sub>		16		
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	25	W	
		T <sub>C</sub> = 100 °C	10		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C	

# HFA08TA60C



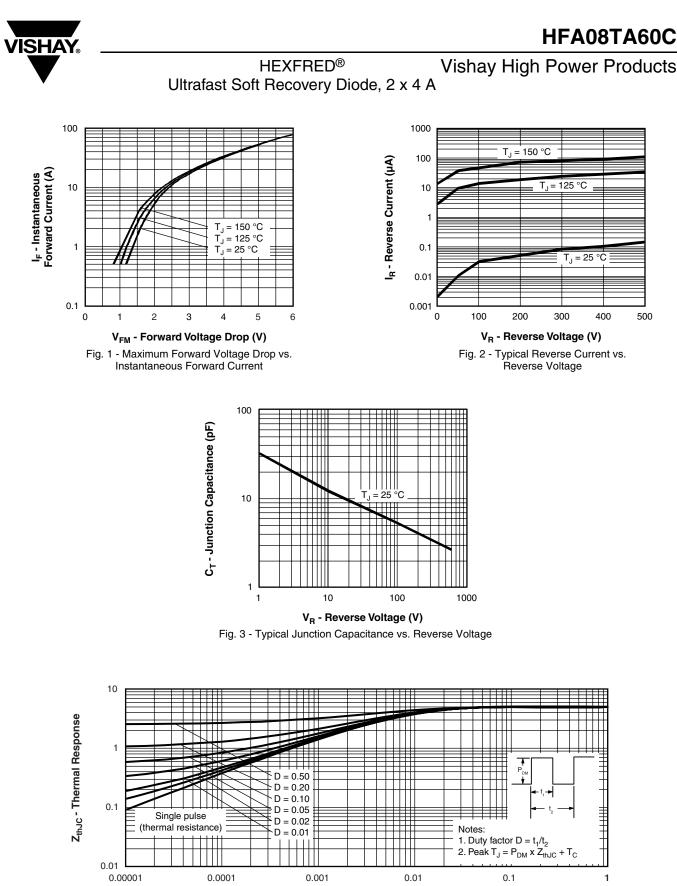
# Vishay High Power Products

### HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 2 x 4 A

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA		600	-	-	
Maximum forward voltage V <sub>FM</sub>		I <sub>F</sub> = 4.0 A		-	1.5	1.8	v
	I <sub>F</sub> = 8.0 A	See fig. 1	-	1.8	2.2		
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C	-	-	1.4	1.7	
Maximum reverse		$V_{R} = V_{R}$ rated	Coo fig. 0	-	0.17	3.0	
leakage current	IRM	$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	See fig. 2	-	44	300	μΑ
Junction capacitance	CT	V <sub>R</sub> = 200 V	See fig. 3	-	4.0	8.0	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	17	-	
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4.0 A	-	28	42	ns
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	38	57	
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	2.9	5.2	A
See fig. 7 and 8	See fig. 7 and 8 $I_{RRM2}$ $T_J =$	T <sub>J</sub> = 125 °C		-	3.7	6.7	
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	40	60	
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105	nC
Peak rate of fall of recovery current during t <sub>b</sub>	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	A/µs
See fig. 11 and 12 $dI_{(rec)M}/dt2 = 125 \text{ °C}$		-	235	-	-7,μ5		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0	
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ⋅ cm (lbf ⋅ in)
Marking device		Case style TO-220AB		HFA08	TA60C	•



t<sub>1</sub> - Rectangular Pulse Duration (s)

Fig. 4 - Maximum Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

# HFA08TA60C

### Vishay High Power Products

HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 2 x 4 A

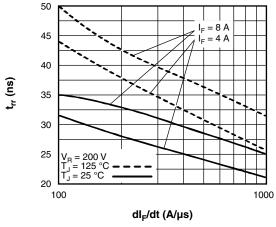
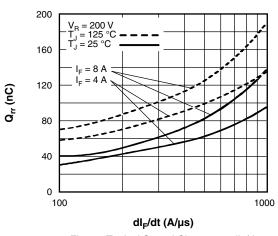
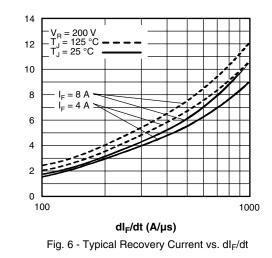


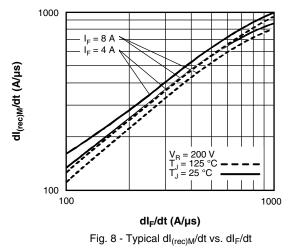
Fig. 5 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 



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Fig. 7 - Typical Stored Charge vs. dI<sub>F</sub>/dt





I<sub>rr</sub> (A)



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Ultrafast Soft Recovery Diode, 2 x 4 A

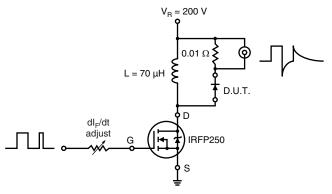


Fig. 9 - Reverse Recovery Parameter Test Circuit

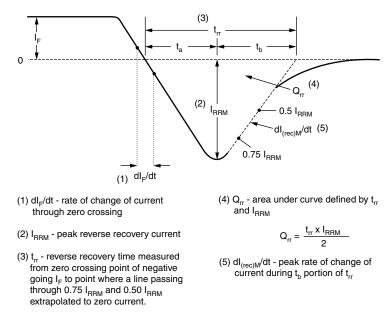


Fig. 10 - Reverse Recovery Waveform and Definitions

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95222				
Part marking information	http://www.vishay.com/doc?95225			



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